Strain relaxation mechanism in the Si-SiO2 system and its influence on the interface properties
Kropman, Daniel; **Mellikov, Enn**; **Öpik, Andres**; **Lott, Kalju**; **Volobujeva, Olga**; Kärner, T.; Heinmaa, I.; Laas, Tõnu; Medvid, A.
Radiation Interaction with Materials and its use in Technologies : Kaunas, 24-27.09.2008 2008 / p. 204-207
https://www.sciencedirect.com/science/article/pii/S0921452609010321